MA MOSPEC

Switchmode Dual Ultrafast Power Rectifiers

... Designed for use in switching power supplies. inverters and as free wheeling diodes. These state-of-the-art devices have the following features.

- * High Surge Capacity
- * Low Power Loss, High efficiency
- * Glass Passivated chip junctions
- * 150 °C Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction
- * Low Forward Voltage, High Current Capability
- * High-Switching Speed 50 Nanosecond Recovery Time
- * Plastic Material used Carries Underwriters Laboratory

MAXIMUM RATINGS

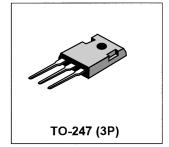
Characteristic	Symbol		U2	:0D		Unit
		30	40	50	60	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	300	400	500	600	V
RMS Reverse Voltage	V _{R(RMS)}	210	280	350	420	V
Average Rectifier Forward Current Per Leg T _c =125°C Per Total Device	I _{F(AV)}		•	0 !0		A
Peak Repetitive Forward Current (Rate V _R ,Square Wave,20kHz,T _c =125°C)	I _{FM}		2	.0		Α
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware,single phase,60Hz)	I _{FSM}		20	00		А
Operating and Storage Junction Temperature Range	T _j , T _{stg}		- 65 to	+ 150		°C

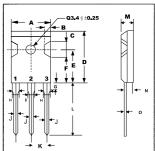
ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	U20D				Unit
		30	40	50	60]
Maximum Instantaneous Forward Voltage $(I_F = 10 \text{ Amp}, T_C = 25 ^{\circ}\text{C})$ $(I_F = 10 \text{ Amp}, T_C = 100 ^{\circ}\text{C})$	V _F		.30 .15	1	50 36	V
Maximum Instantaneous Reverse Current (Rated DC Voltage, T _c = 25 °C) (Rated DC Voltage, T _c = 125 °C)	I _R			10 00		uA
Reverse Recovery Time $(I_F = 0.5 \text{ A}, I_R = 1.0, I_{rr} = 0.25 \text{ A})$	T _{rr}			50		ns
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	C _P		-	70		pF

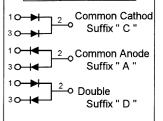
ULTRA FAST RECTIFIERS

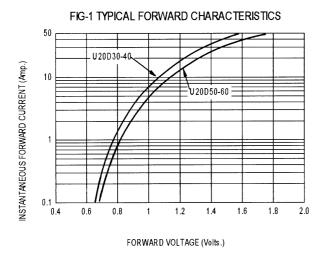
20 AMPERES 300 -- 600 VOLTS



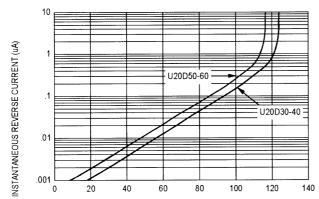


DIM	MILLMETERS		
Dilvi	MIN	MAX	
Α		16.2	
В	1.7	2.7	
С	5.0	6.0	
D		23.0	
Ε	14.8	15.2	
F	11.7	12.7	
G		4.5	
Н		2.5	
- 1		3.5	
J	1.1	1.4	
K	5.25	5.65	
L	19		
М	4.7	5.3	
N	2.8	3.2	
0	0.45	0.85	

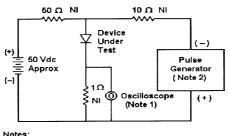




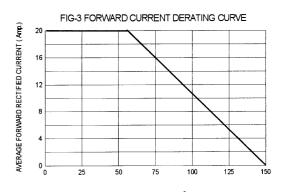


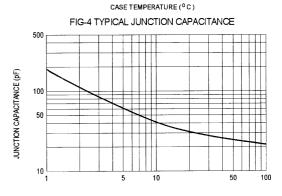


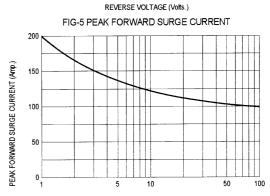
PERCENT OF PEAK REVERSE VOLTAGE(%)

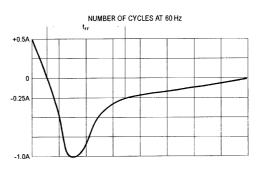


Notes: 1. Rise Time = 7 ns max. Input Impedance =1 M Ω , 22 pF 2. Rise Time = 10 ns max. Input Impedance = 50 Ω









Set time base for 10/20 ns/div

Fig-6 Reverse Recovery Time Characteristic and Test Circuit Diagram



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